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PTO/SB/21 (08-00)

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TRANSMITTAL FORM

(to be used for all correspondence after initial filing)

Application Number	10/648,434		
	Filing Date	August 27, 2003	
	First Named Inventor	DABRAL, Sanjay	
	Group Art Unit	2822	
	Examiner Name	To Be Assigned	
Total Number of Pages in This Submission	7	Attorney Docket Number	2207/597504

ENCLOSURES (check all that apply)

<input type="checkbox"/> Fee Transmittal Form <input type="checkbox"/> Fee Attached <input type="checkbox"/> Amendment / Response <input type="checkbox"/> After Final <input type="checkbox"/> Affidavits/declaration(s) <input type="checkbox"/> Extension of Time Request <input type="checkbox"/> Express Abandonment Request <input checked="" type="checkbox"/> Information Disclosure Statement <input type="checkbox"/> Certified Copy of Priority Document(s) <input type="checkbox"/> Response to Missing Parts/Incomplete Application <input type="checkbox"/> Response to Missing Parts under 37 CFR 1.52 or 1.53	<input type="checkbox"/> Assignment Papers (for an Application) <input type="checkbox"/> Drawing(s) <input type="checkbox"/> Licensing-related Papers <input type="checkbox"/> Petition <input type="checkbox"/> Petition to Convert to a Provisional Application <input type="checkbox"/> Power of Attorney, Revocation Change of Correspondence Address <input type="checkbox"/> Terminal Disclaimer <input type="checkbox"/> Request for Refund <input type="checkbox"/> CD, Number of CD(s)	<input type="checkbox"/> After Allowance Communication to Group <input type="checkbox"/> Appeal Communication to Board of Appeals and Interferences <input type="checkbox"/> Appeal Communication to Group (Appeal Notice, Brief, Reply Brief) <input type="checkbox"/> Proprietary Information <input type="checkbox"/> Status Letter <input type="checkbox"/> Other Enclosure(s) (please identify below):
Remarks		

SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT

Firm or Individual name	Kenyon & Kenyon B. Delano Jordan Registration No. 43,698
Signature	
Date	December 2, 2003

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PATENT APPLICATION

2207/597504

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Assignee: INTEL CORPORATION
Application No.: 10/648,434
Applicant: SANJAY DABRAL et al.
Filed: August 27, 2003
TC/ Art Unit: 2822
Examiner: TO BE ASSIGNED
Docket No.: 2207/597504
Customer No.: 23838
For: ENHANCED CONDUCTIVITY BODY BIASED PMOS DRIVER

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:


Pursuant to 37 CFR § 1.56, the attention of the Patent and Trademark Office is hereby directed to the reference(s) listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the reference(s) be made of record therein and appear among the "References Cited" on any patent to issue therefrom. The paragraphs marked below are applicable.

- ☐ 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date or the date of filing a CPA, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- ☐ 2. This Information Disclosure Statement is being filed with a Request for Continued Examination (RCE). No certification or fee is required.
- ☐ 3. This Information Disclosure Statement is being filed more than three months after the U.S. filing date AND after the mailing date of the first Office Action on the merits, but before the mailing date of a Final Rejection or Notice of Allowance.

- ☐ a. I hereby certify that each item of information contained in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement. 37 CFR §1.97(e)(1).
- ☐ b. I hereby certify that no item of information in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to my knowledge after making reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this Information Disclosure Statement. 37 CFR §1.97(e)(2).
- ☐ c. Please debit Deposit Account No. 11-0600 in the amount of \$240.00 in payment of the fee under 37 CFR §1.17(p) to ensure consideration of the disclosed information. Two duplicate copies of this paper are attached.
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- ☐ 5. The reference(s) was/were cited by or submitted to the Office in parent application No.09/475,648, filed December 30, 1999, application No. 10/314,308 filed on December 9, 2003 and application No. 10/314,309, filed on December 9, 2003, which are relied upon for an earlier filing date under 35 U.S.C. §120. Thus, copies of these references are not attached. 37 CFR §1.98(d).

Respectfully submitted,

KENYON & KENYON


B. Delano Jordan
Registration No. 43,698

Date: December 2, 2003

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STATEMENT BY APPLICANT**

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Sheet 1 of 4

Complete if Known

Application Number	10/648,434
Filing Date	August 27, 2003
First Named Inventor	Sanjay DABRAL
Group Art Unit	2822
Examiner Name	Not Yet Assigned
Attorney Docket Number	2207/597504

U.S. PATENT DOCUMENTS

Examiner Initials *	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
		US- 5,461,338	10-24-95	Hirayama et al.	
		US- 5,557,231	09-17-96	Yamaguchi et al.	
		US- 5,559,368	09-24-96	Hu et al.	
		US- 5,689,144	11-18-97	Williams	
		US- 5,689,209	11-18-97	Williams et al.	
		US- 6,493,430	12-10-02	Leuca et al.	
		US- 6,100,751	08-08-00	De et al.	
		US- 6,218,895	04-17-01	De et al.	
		US- 6,300,819	10-09-01	De et al.	
		US- 6,166,584	12-26-00	De et al.	
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FOREIGN PATENT DOCUMENTS

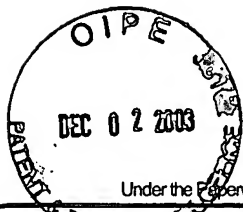
Examiner Initials *	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)				
		WO 98/59419	16 JUNE 1998	DE et al.		

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First Named Inventor	Sanjay DABRAL et al.
Group Art Unit	2822
Examiner Name	TO BE ASSIGNED
Attorney Docket Number	2207/597504

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

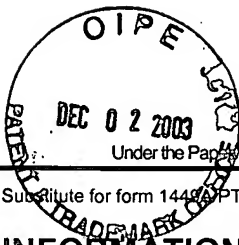
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		Excerpt from "1996 IEEE International SOI Conference Proceedings" (October 1996) p. 141.	
		ANTONIADIS, D.A. and CHUNG, J.E., "Physics And Technology Of Ultra Short Channel MOSFET Devices", <i>IEDM Technical Digest</i> (1991) pp. 2.1.1 - 2.1.4.	
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Examiner Signature	Date Considered
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Sheet 3 of 4

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Application Number	10/648,434
Filing Date	August 27, 2003
First Named Inventor	Sanjay DABRAL et al.
Group Art Unit	2822
Examiner Name	TO BE ASSIGNED
Attorney Docket Number	2207/597504

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

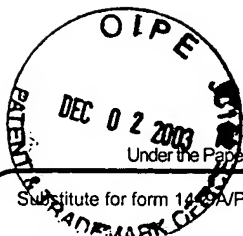
Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		KURODA, T. et al., "A 0.9-V, 150-MHz, 10-mW, 4mm ² , 2-D Discrete Cosine Transform Core Processor With Variable Threshold-Voltage (VT) Scheme", <i>IEEE Journal of Solid-State Circuits</i> , Vol. 31, No. 11 (November 1996) pp. 1770-1779.	
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Examiner
SignatureDate
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Sheet 4 of 4

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		WALKER, W. et al., "Design And Analysis Of A CMOS SOS/SOI Receiver For A Radiation Hard Computer", <i>IEEE SOS/SOI Technology Conference</i> , (October 1989) pp. 167-168.	
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		"WANN, Clement H. et al., "A Comparative Study of Advanced MOSFET Concepts", <i>IEEE Transactions On Electron Devices</i> , Vol. 43, No. 10, (October 1996) pp. 1742-1751 .	
		WILLIAMS, R. et al., "MOSFET Flyback-Diode Conduction and dV/dt Effects in Power ICs in Low-Voltage Motor Control Applications", <i>Proceedings of the 3rd International Symposium on Power Semiconductor Devices and ICs</i> ", (June 1991), pp. 254-257.	

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